1. General description

PNP low V_{CEsat} transistor and NPN Resistor-Equipped Transistor (RET) in a SOT457 (SC-74) small Surface Mounted Device (SMD) plastic package.

2. Features and benefits

- Low V_{CEsat} transistor and resistor-equipped transistor in one package
- Low threshold voltage (< 1 V) compared to MOSFET
- · Low drive power required
- Space-saving solution
- · Reduction of component count
- AEC-Q101 qualified

3. Applications

- · Supply line switches
- · Battery charger switches
- · High-side switches for LEDs, drivers and backlights
- Portable equipment

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|-----|-----|------|
| TR1; PNP low | V _{CEsat} transistor | | | | | | |
| V _{CEO} | collector-emitter voltage | open base | | - | - | -60 | V |
| I _C | collector current | | [1] | - | - | -1 | Α |
| R _{CEsat} | collector-emitter saturation resistance | I_C = -1 A; I_B = -100 mA; T_{amb} = 25 °C; pulsed; t_p ≤ 300 μs; δ_{factor} ≤ 0.02 | | - | 255 | 340 | mΩ |
| TR2; NPN res | istor-equipped transisto | or | | | | | |
| V _{CEO} | collector-emitter voltage | open base | | - | - | 50 | V |
| Io | output current | | | - | - | 100 | mA |
| R1 | bias resistor 1 (input) | | | 7 | 10 | 13 | kΩ |
| R2/R1 | bias resistor ratio | | | 0.8 | 1 | 1.2 | |

^[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



60 V, 1 A PNP loadswitch double transistor

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|------------------------|----------------------------------|--------------------|
| 1 | E1 | emitter TR1 | | C1 I2 GND2 |
| 2 | B1 | base TR1 | | |
| 3 | O2 | output (collector) TR2 | <u> </u> | R1 R2 |
| 4 | GND2 | GND (emitter) TR2 | | TR2 |
| 5 | 12 | input (base) TR2 | <u>∃</u> 1 <u>∃</u> 2 <u>∃</u> 3 | TRI |
| 6 | C1 | collector TR1 | TSOP6 (SOT457) | E1 B1 O2 sym036 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|--|---------------|--|--|
| | Name | Description | Version | | |
| PBLS6003D | TSOP6 | plastic, surface-mounted package (SC-74; TSOP6); 6 leads | <u>SOT457</u> | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| | - |
| PBLS6003D | F3 |

60 V, 1 A PNP loadswitch double transistor

8. Limiting values

Table 5. Limiting values

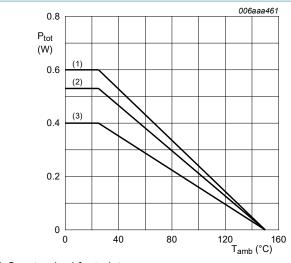
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------------|-------------------------------------|-----|-----|------|------|
| TR1; PNP lo | w V _{CEsat} transistor | | | | | _ |
| V _{CBO} | collector-base voltage | open emitter | | - | -80 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | -60 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | -5 | V |
| I _C | collector current | | [1] | - | -700 | mA |
| | | | [2] | - | -850 | mA |
| | | | [3] | - | -1 | Α |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | -2 | Α |
| I _B | base current | | | - | -300 | mA |
| I _{BM} | peak base current | single pulse; t _p ≤ 1 ms | | - | -1 | Α |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 250 | mW |
| | | | [2] | - | 350 | mW |
| | | | [3] | - | 400 | mW |
| TR2; NPN re | esistor-equipped transistor | | , | ' | | |
| V _{CBO} | collector-base voltage | open emitter | | - | 50 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | 50 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | 10 | V |
| VI | input voltage | | | -10 | 40 | V |
| Io | output current | | | - | 100 | mA |
| I _{CM} | peak collector current | | | - | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 200 | mW |
| | | | [2] | - | 200 | mW |
| | | | [3] | - | 200 | mW |
| Per device | | | , | | | |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 400 | mW |
| 101 | | | [2] | - | 530 | mW |
| | | | [3] | - | 600 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -65 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm 2 . Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

60 V, 1 A PNP loadswitch double transistor



- (1) Ceramic PCB, Al₂O₃, standard footprint (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Power derating curves Fig. 1.

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|--|------------|-----|-----|-----|-----|------|
| Per device | <u>'</u> | | ' | | | | |
| R _{th(j-a)} | thermal resistance from | | [1] | - | - | 312 | K/W |
| junction to ambie | junction to ambient | | [2] | - | - | 236 | K/W |
| | | | [3] | - | - | 208 | K/W |
| TR1; PNP lo | w V _{CEsat} transistor | | , | | | | |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | | - | - | 105 | K/W |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

60 V, 1 A PNP loadswitch double transistor

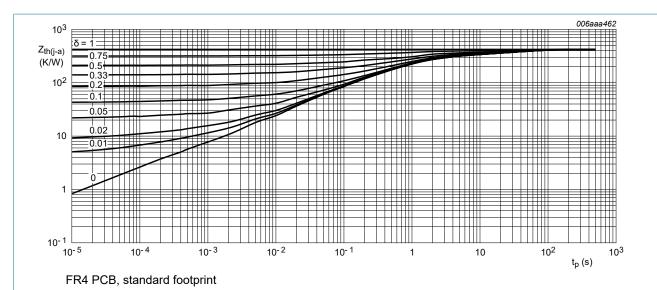


Fig. 2. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

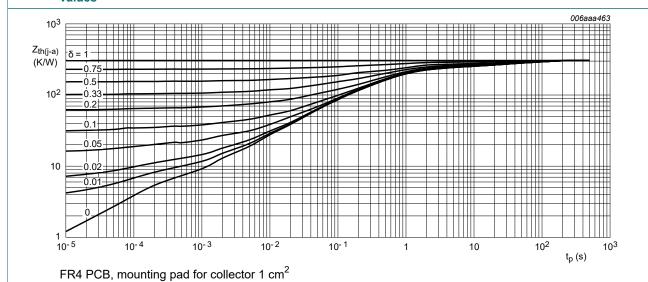


Fig. 3. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 1 A PNP loadswitch double transistor

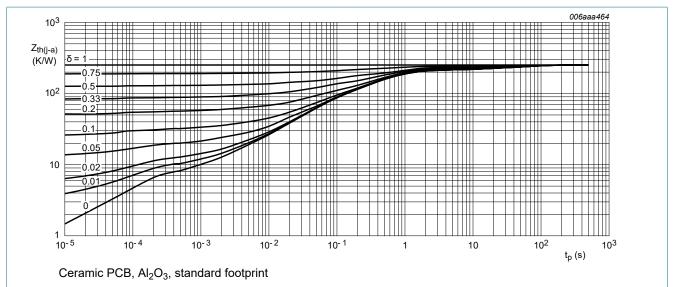


Fig. 4. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-------|------|------|
| TR1; PNP Io | ow V _{CEsat} transistor | | | | ' | ' |
| I _{CBO} | collector-base cut-off | $V_{CB} = -60 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$ | - | - | -100 | nA |
| | current | V _{CB} = -60 V; I _E = 0 A; T _j = 150 °C | - | - | -50 | μA |
| I _{CES} | collector-emitter cut-off current | V _{CE} = -60 V; V _{BE} = 0 V; T _{amb} = 25 °C | - | - | -100 | nA |
| I _{EBO} | emitter-base cut-off current | V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C | - | - | -100 | nA |
| h _{FE} | DC current gain | V_{CE} = -5 V; I_{C} = -1 mA; T_{amb} = 25 °C | 200 | 350 | - | |
| | | V_{CE} = -5 V; I_{C} = -500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 150 | 230 | - | |
| | | V_{CE} = -5 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; TR1; PNP low V_{CEsat} transistor; T_{amb} = 25 °C | 100 | 160 | - | |
| - CESat | collector-emitter | I_C = -100 mA; I_B = -1 mA; T_{amb} = 25 °C | - | -110 | -175 | mV |
| | saturation voltage | I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | -135 | -180 | mV |
| | | I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | -255 | -340 | mV |
| R _{CEsat} | collector-emitter saturation resistance | I_C = -1 A; I_B = -100 mA; T_{amb} = 25 °C; pulsed; $t_p \le 300$ μs; $\delta_{factor} \le 0.02$ | - | 255 | 340 | mΩ |
| V _{BEsat} | base-emitter saturation voltage | I_C = -1 A; I_B = -50 mA; T_{amb} = 25 °C; pulsed; $t_p \le 300$ μs; $\delta_{factor} \le 0.02$ | - | -0.95 | -1.1 | V |
| V_{BEon} | base-emitter turn-on voltage | V_{CE} = -5 V; I_{C} = -1 A; T_{amb} = 25 °C; pulsed; t_{p} ≤ 300 μs; δ_{factor} ≤ 0.02 | - | -0.82 | -0.9 | V |

60 V, 1 A PNP loadswitch double transistor

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|--------------------------------------|---|-----|-----|-----|------|
| t _d | delay time | I _C = -0.5 A; | - | 11 | - | ns |
| t _r | rise time | I _{Bon} = -25 mA; I _{Boff} = 25 mA; | - | 30 | - | ns |
| t _{on} | turn-on time | $T_{amb} = 25 ^{\circ}C$ | - | 41 | - | ns |
| t _s | storage time |] | - | 205 | - | ns |
| t _f | fall time | | - | 55 | - | ns |
| t _{off} | turn-off time | | - | 260 | - | ns |
| C _c | collector capacitance | V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C | - | 9 | 15 | pF |
| f _T | transition frequency | V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C | 150 | 185 | - | MHz |
| TR2; NPN r | esistor-equipped transisto | r | | | | |
| I _{CBO} | collector-base cut-off current | V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| I _{CEO} | collector-emitter cut-off | V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C | - | - | 1 | μA |
| | current | V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C | - | - | 50 | μA |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ | - | - | 400 | μΑ |
| h _{FE} | DC current gain | V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C | 30 | - | - | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ | - | - | 150 | mV |
| $V_{I(off)}$ | off-state input voltage | V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C | - | 1.1 | 0.8 | V |
| $V_{I(on)}$ | on-state input voltage | V _{CE} = 0.3 V; I _C = 10 mA; T _{amb} = 25 °C | 2.5 | 1.8 | - | V |
| R1 | bias resistor 1 (input) | | 7 | 10 | 13 | kΩ |
| R2/R1 | bias resistor ratio | | 0.8 | 1 | 1.2 | |
| C _c | collector capacitance | V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C | - | - | 2.5 | pF |

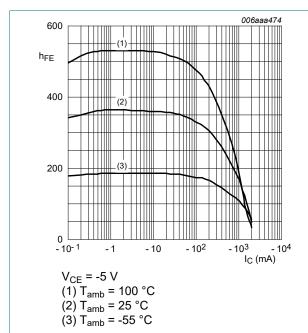


Fig. 5. TR1 (PNP): DC current gain as a function of collector current; typical values

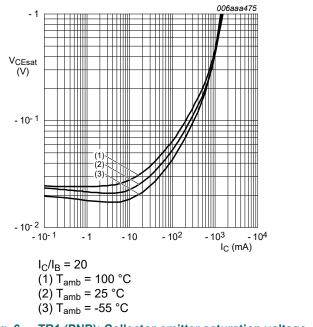


Fig. 6. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

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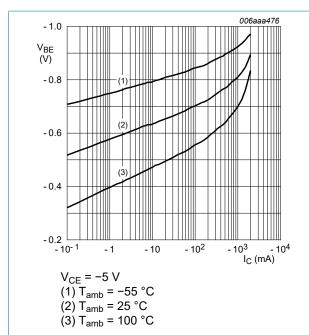


Fig. 7. TR1 (PNP): Base-emitter voltage as a function of collector current; typical values

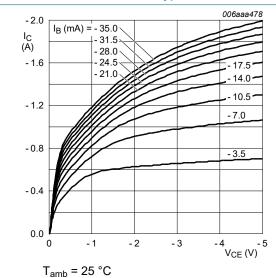
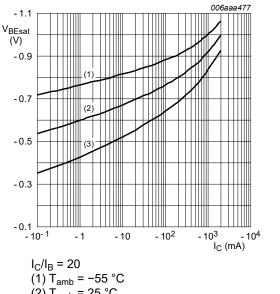
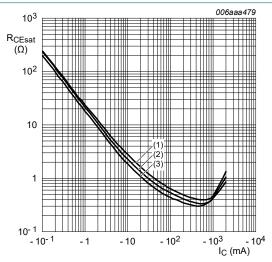


Fig. 9. TR1 (PNP): Collector current as a function of collector-emitter voltage; typical values



(1) T_{amb} = -55 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 8. TR1 (PNP): Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$ (1) T_{amb} = 100 °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 1 A PNP loadswitch double transistor

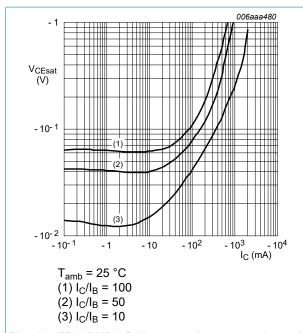
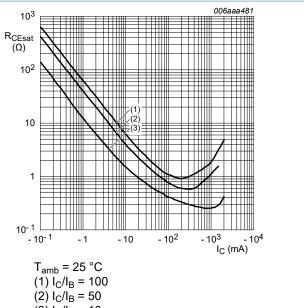


Fig. 11. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



(2) $I_C/I_B = 50$ (3) $I_C/I_B = 10$

Fig. 12. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

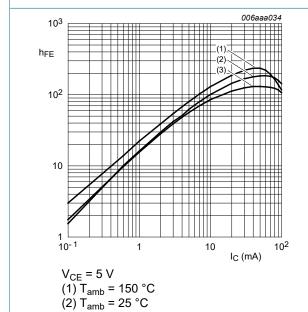
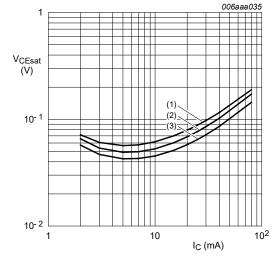


Fig. 13. TR2 (NPN): DC current gain as a function of collector current; typical values

(3) $T_{amb} = -40 \, ^{\circ}C$

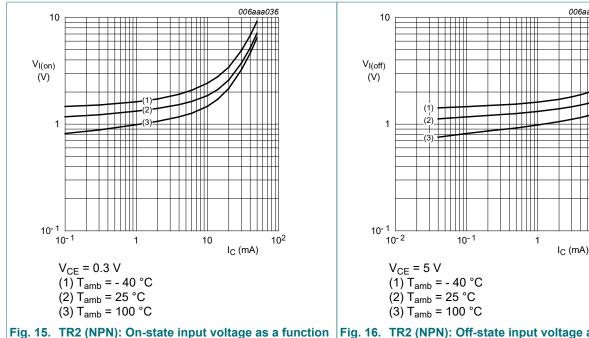


 $I_C/I_B = 20$ (1) T_{amb} = 100 °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 14. TR2 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

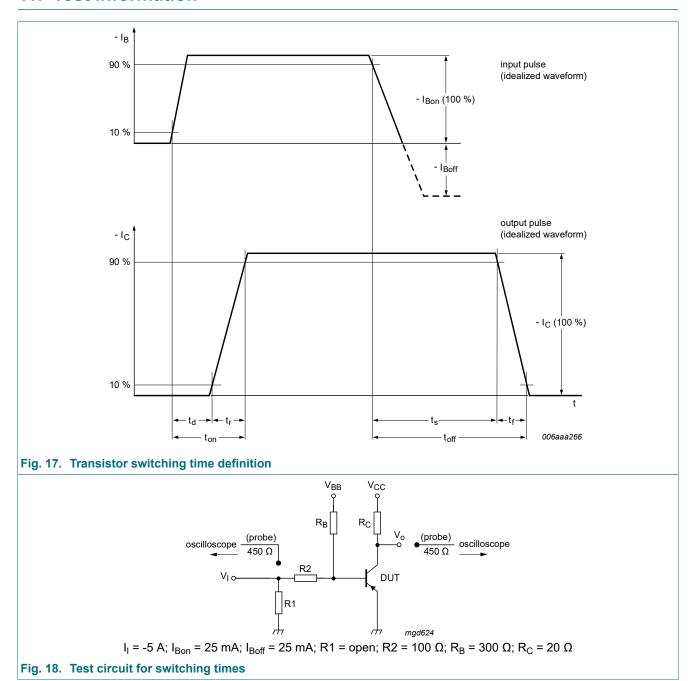
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11. Test information

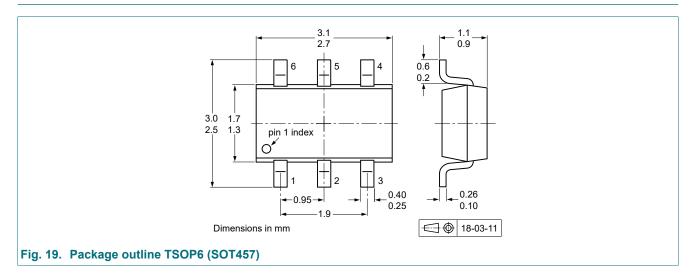


Quality information

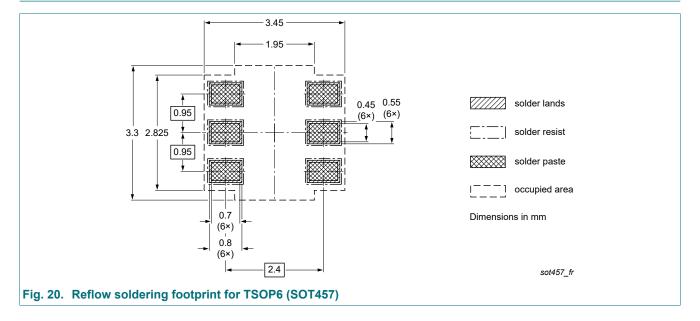
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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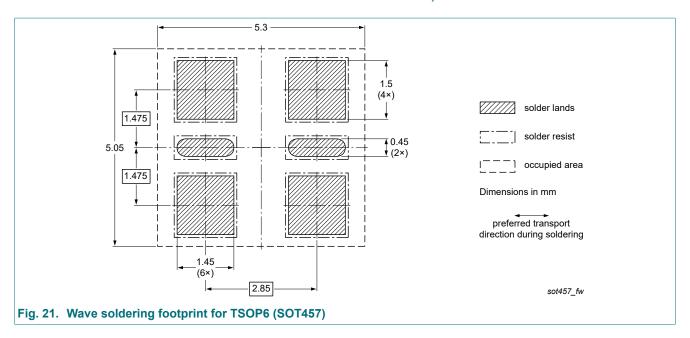
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | |
|----------------|---|--------------------|---------------|-------------|--|
| PBLS6003D v.3 | 20230830 | Product data sheet | - | PBLS6003D_2 | |
| Modifications: | The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. | | | | |
| PBLS6003D_2 | 20090907 | Product data sheet | - | PBLS6003D_1 | |
| PBLS6003D_1 | 20050628 | Product data sheet | - | - | |

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PBLS6003E

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 30 August 2023

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